

What is claimed is:

*Sub B1* →  
5 1. A thin film transistor comprising:  
an insulator substrate;  
a gate electrode located on the insulator substrate;  
a gate insulator film provided above the insulator  
substrate and the gate electrode; and  
a polycrystalline silicon film located on the gate  
insulator film, the polycrystalline silicon film being  
*fig. 9* 112 *let* [formed by irradiating a laser beam on a surface of an  
10 amorphous silicon film to heat the amorphous silicon film],  
the gate electrode having a center portion with a flat  
surface and a pair of tapered end portions with inclined  
surfaces, an angle between each of the inclined surfaces of  
the pair of tapered end portions and a surface of the  
insulator substrate being set within a range of 5° to 40° so  
that [a uniform grain size of the polycrystalline silicon  
5 film is acquired by securing a gate withstand voltage of the  
112 *let* thin film transistor and preventing the inclined surfaces of  
the pair of tapered end portions from increasing], wherein  
10 [the laser beam is scanned on the surface of the amorphous  
silicon film such that laser energy increases in order of  
112 *let* the substrate, one of the pair of tapered end portions, and  
the center portion].

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